

## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON) \max}$	Package	$I_D$ $T_A = +25^\circ\text{C}$
-20V	0.9Ω @ $V_{GS} = -4.5\text{V}$	SOT23	-430mA
	2.0Ω @ $V_{GS} = -1.8\text{V}$		-150mA

## Description

This new generation MOSFET has been designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

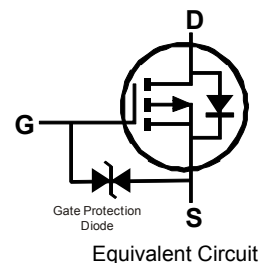
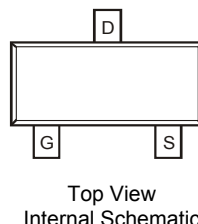
- DC-DC Converters
- Power Management Functions

## Features

- Low On-Resistance
- Very Low Gate Threshold Voltage  $V_{GS(TH)} < 1\text{V}$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- ESD Protected Gate
- Qualified to AEC-Q101 standards for High Reliability

## Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding
- Compound: UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin annealed over Copper leadframe.
- Solderable per MIL-STD-202, Method 208 Ⓔ③
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)

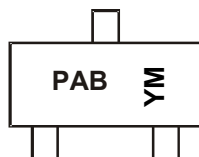


## Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMP2004K-7	Standard	SOT23	3,000/Tape & Reel
DMP2004KQ-7	Automotive	SOT23	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



PAB = Product Type Marking Code  
YM = Date Code Marking  
Y = Year (ex: B = 2014)  
M = Month (ex: 9 = September)

### Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015
Code	V	W	X	Y	Z	A	B	C

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V <sub>DSS</sub>	-20	V
Gate-Source Voltage	V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V	I <sub>D</sub>	-600	mA
Pulsed Drain Current	I <sub>DM</sub>	-1.9	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P <sub>D</sub>	550	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	227	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1	μA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±1.0	μA	V <sub>GS</sub> = ±4.5V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 6)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.5	—	-1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	0.7	0.9	Ω	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -430mA
		—	1.1	1.4		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -300mA
		—	1.7	2.0		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -150mA
Forward Transfer Admittance	Y <sub>fs</sub>	200	—	—	mS	V <sub>DS</sub> = -10V, I <sub>D</sub> = -0.2A
Diode Forward Voltage (Note 6)	V <sub>SD</sub>	-0.5	—	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -115mA
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Input Capacitance	C <sub>iss</sub>	—	—	175	pF	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	—	30	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	—	20	pF	
Turn-On Delay Time	t <sub>D(on)</sub>	—	8.5	—	ns	V <sub>DD</sub> = -3V, V <sub>GS</sub> = -2.5V, R <sub>L</sub> = 300Ω, R <sub>G</sub> = 25Ω, I <sub>D</sub> = -100mA
Turn-On Rise Time	t <sub>r</sub>	—	4.3	—	ns	
Turn-Off Delay Time	t <sub>D(off)</sub>	—	20.2	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	19.2	—	ns	

Notes: 5. Device mounted on FR-4 PCB.  
6. Short duration pulse test used to minimize self-heating effect.  
7. Guaranteed by design. Not subject to product testing.

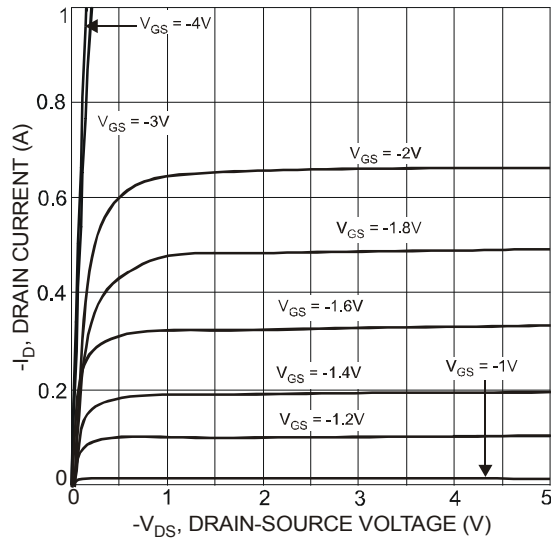


Figure 1 Typical Output Characteristics

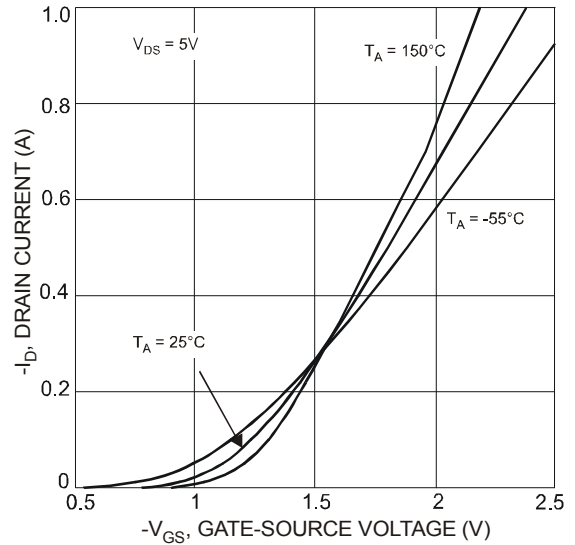


Figure 2 Typical Transfer Characteristics

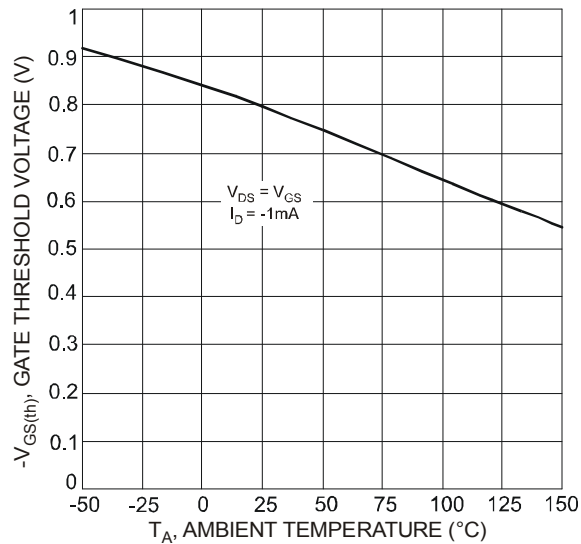


Figure 3 Gate Threshold Voltage vs. Ambient Temperature

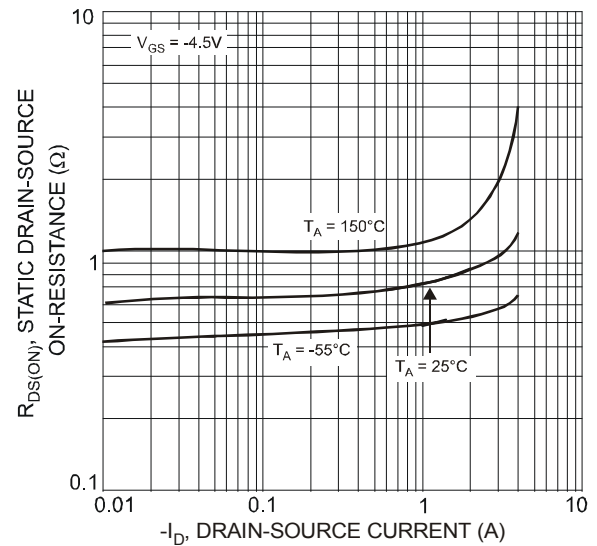


Figure 4 Static Drain-Source On-Resistance vs. Drain Current

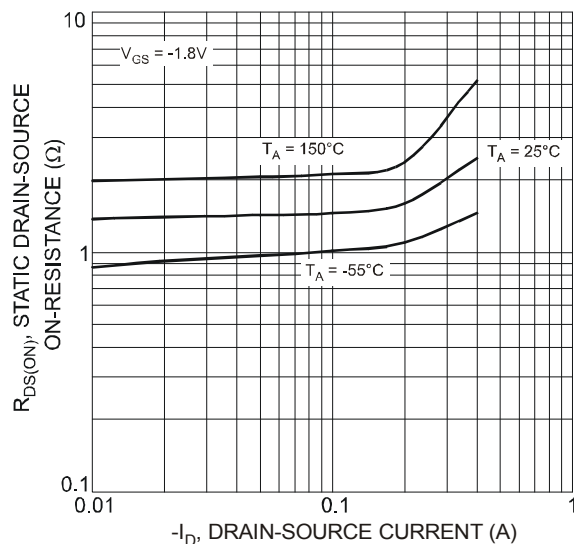


Figure 5 Static Drain-Source On-Resistance vs. Drain Current

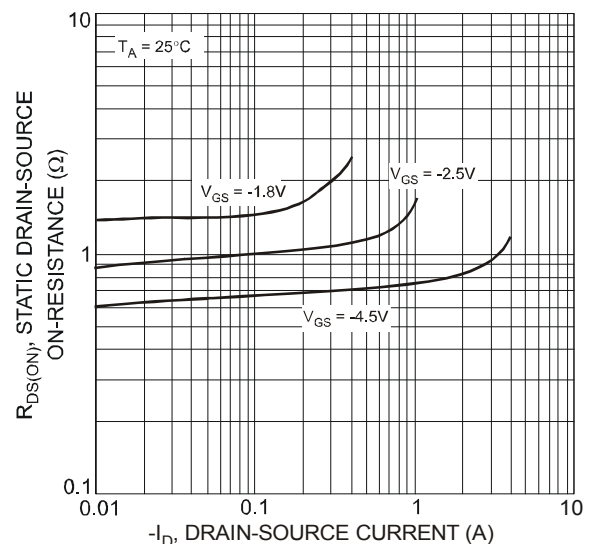


Figure 6 Static Drain-Source On-Resistance vs. Drain-Source Current

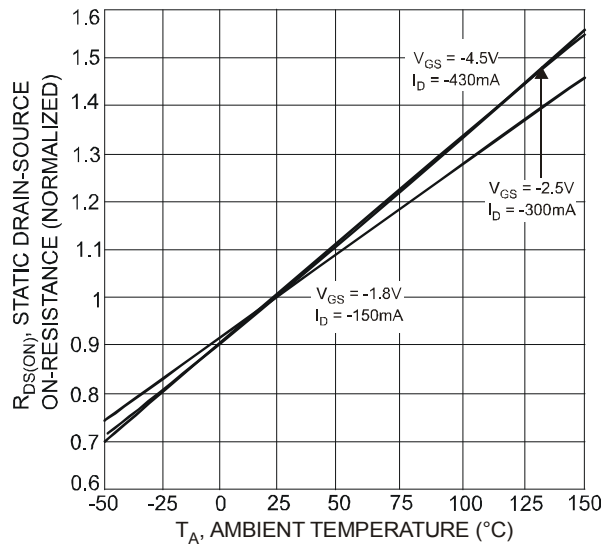


Figure 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

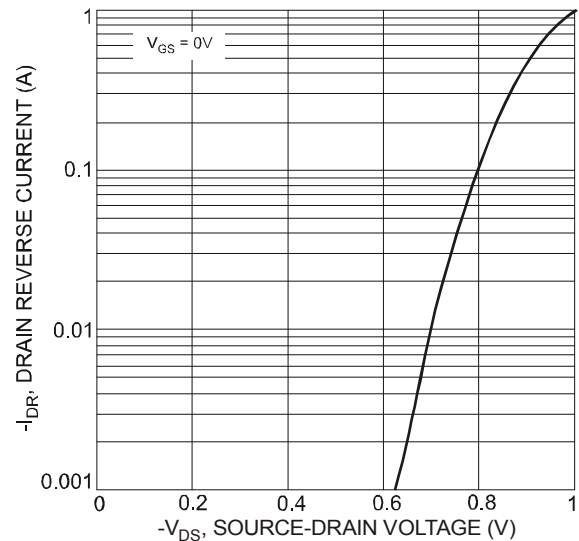


Figure 8 Reverse Drain Current vs. Source-Drain Voltage

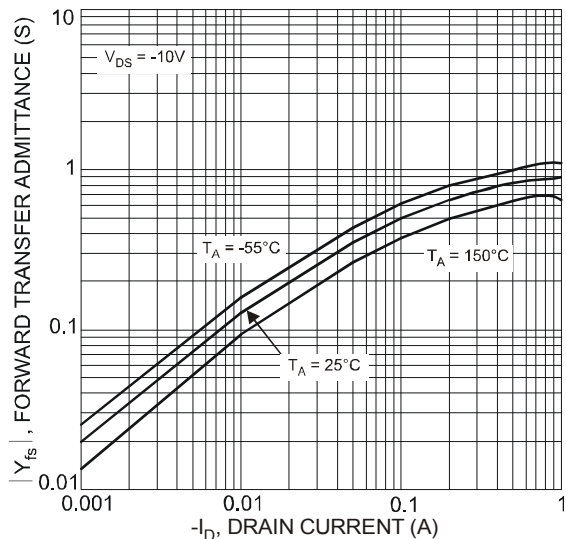


Figure 9 Forward Transfer Admittance vs. Drain Current

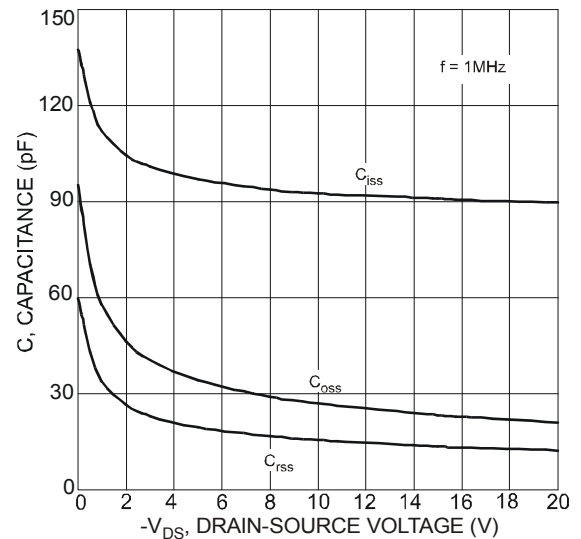
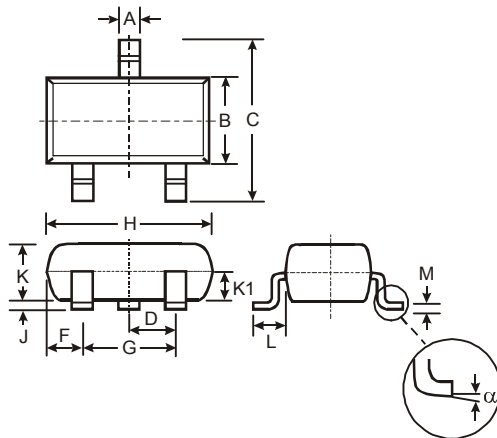


Figure 10 Typical Capacitance

## Package Outline Dimensions

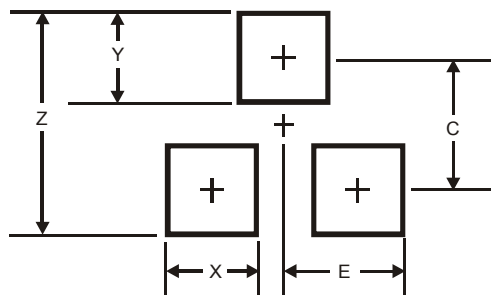
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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